

Description

The advanced, ultra-low power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP1G08 is a single, two-input, positive AND gate with a standard push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

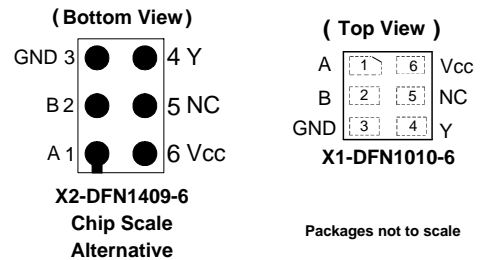
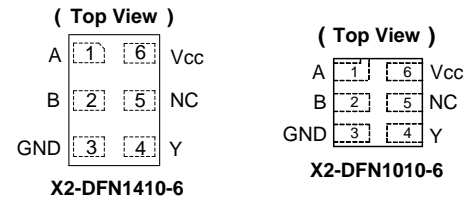
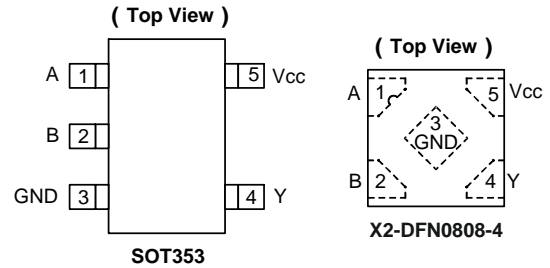
$$Y = A \bullet B \text{ or } Y = \overline{\overline{A} + \overline{B}}$$

Features

- Advanced Ultra-Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
 - I_{CC} < 0.9µA
- Low Dynamic Power Consumption
 - C_{PD} = 6.3 pF (Typical at 3.6V)
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time. The hysteresis is typically 250mV at V_{CC} = 3.0V.
- I_{OFF} Supports Partial Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 - 2000V Human Body Model (A114)
 - Exceeds 1000V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless packages named per JESD30E
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony- Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

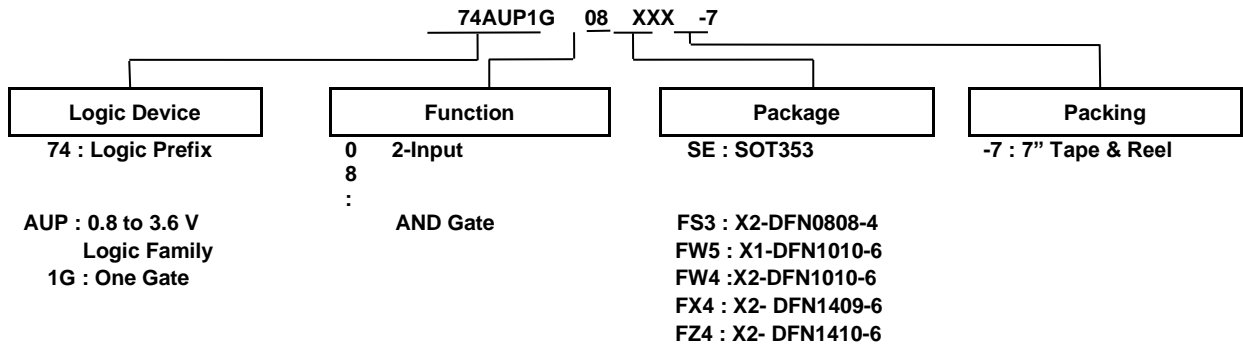
Pin Assignments



Applications

- Suited for battery and low-power requirements
- Wide array of products such as:
 - Tablets, e-readers
 - Cell phones, personal navigation/GPS Systems
 - MP3 players, cameras, video recorders
 - PCs, Ultrabook™, notebooks, netbooks
 - Computer peripherals, hard drives, SSDs, CD/DVD ROMs
 - TVs, DVDs, DVRs, set-top boxes

Ordering Information



Orderable Part Number	Package Code	Package (Notes 4 & 5)	Package Size	Packing		
				Quantity	Carrier	Part Number Suffix
74AUP1G08SE-7	SE	SOT353	2.15mm x 2.1mm x 1.1mm 0.65 mm lead pitch	3,000	7" Tape and Reel	-7
74AUP1G08FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.30mm 0.5 mm pad pitch (diamond)	5,000	7" Tape and Reel	-7
74AUP1G08FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000	7" Tape and Reel	-7
74AUP1G08FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000	7" Tape and Reel	-7
74AUP1G08FW4-7R	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000	7" Tape and Reel	-7R
74AUP1G08FX4-7	FX4	X2-DFN1409-6 Chip scale alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000	7" Tape and Reel	-7
74AUP1G08FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000	7" Tape and Reel	-7

Notes: 4. Pad layout, as shown in our suggested pad layouts, can be found at <http://www.diodes.com/package-outlines.html>.
5. The taping orientation is located on our website at <https://www.diodes.com/assets/Packaging-Support-Docs/AP02007.pdf>.

Pin Descriptions

Pin Name	Function
A	Data Input
B	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage

Logic Diagram



Function Table

Inputs		Output
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

Absolute Maximum Ratings (Notes 6 & 7) (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V_{CC}	Supply Voltage Range	-0.5 to +4.6	V
V_I	Input Voltage Range	-0.5 to +4.6	V
V_O	Voltage applied to output in High or Low State	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	Input Clamp Current ($V_I < 0$)	50	mA
I_{OK}	Output Clamp Current ($V_O < 0$)	50	mA
I_O	Continuous Output Current ($V_O = 0$ to V_{CC})	± 20	mA
I_{CC}	Continuous Current Through V_{CC}	50	mA
I_{GND}	Continuous Current Through GND	-50	mA
T_J	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^\circ\text{C}$

- Notes:
- Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
 - Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8) (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit	
V_{CC}	Operating Voltage	0.8	3.6	V	
V_I	Input Voltage	0	3.6	V	
V_O	Output Voltage	0	V_{CC}	V	
I_{OH}	High-Level Output Current	$V_{CC} = 0.8\text{V}$	—	-20	μA
		$V_{CC} = 1.1\text{V}$	—	-1.1	mA
		$V_{CC} = 1.4\text{V}$	—	-1.7	
		$V_{CC} = 1.65\text{V}$	—	-1.9	
		$V_{CC} = 2.3\text{V}$	—	-3.1	
		$V_{CC} = 3.0\text{V}$	—	-4	
I_{OL}	Low-Level Output Current	$V_{CC} = 0.8\text{V}$	—	20	μA
		$V_{CC} = 1.1\text{V}$	—	1.1	mA
		$V_{CC} = 1.4\text{V}$	—	1.7	
		$V_{CC} = 1.65\text{V}$	—	1.9	
		$V_{CC} = 2.3\text{V}$	—	3.1	
		$V_{CC} = 3.0\text{V}$	—	4	
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	$V_{CC} = 0.8\text{V}$ to 3.6V	—	200	ns/V
T_A	Operating Free-Air Temperature	-40	+125	$^\circ\text{C}$	

- Note: 8. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vcc	$T_A = +25^\circ\text{C}$		$T_A = -40^\circ\text{C to } +85^\circ\text{C}$		Unit
				Min	Max	Min	Max	
V_{IH}	High-Level Input Voltage	—	0.8V to 1.65V	$0.80 \times V_{CC}$	—	$0.80 \times V_{CC}$	—	V
		—	1.65V to 1.95V	$0.65 \times V_{CC}$	—	$0.65 \times V_{CC}$	—	
		—	2.3V to 2.7V	1.6	—	1.6	—	
		—	3.0V to 3.6V	2.0	—	2.0	—	
V_{IL}	Low-Level Input Voltage	—	0.8V to 1.65V	—	$0.30 \times V_{CC}$	—	$0.30 \times V_{CC}$	V
		—	1.65V to 1.95V	—	$0.35 \times V_{CC}$	—	$0.35 \times V_{CC}$	
		—	2.3V to 2.7V	—	0.7	—	0.7	
		—	3.0V to 3.6V	—	0.9	—	0.9	
V_{OH}	High-Level Output Voltage	$I_{OH} = -20\mu\text{A}$	0.8V to 3.6V	$V_{CC} - 0.1$	—	$V_{CC} - 0.1$	—	V
		$I_{OH} = -1.1\text{mA}$	1.1V	$0.75 \times V_{CC}$	—	$0.7 \times V_{CC}$	—	
		$I_{OH} = -1.7\text{mA}$	1.4V	1.11	—	1.03	—	
		$I_{OH} = -1.9\text{mA}$	1.65V	1.32	—	1.3	—	
		$I_{OH} = -2.3\text{mA}$	2.3V	2.05	—	1.97	—	
		$I_{OH} = -3.1\text{mA}$		1.9	—	1.85	—	
		$I_{OH} = -2.7\text{mA}$	3V	2.72	—	2.67	—	
		$I_{OH} = -4\text{mA}$		2.6	—	2.55	—	
V_{OL}	Low-Level Output Voltage	$I_{OL} = 20\mu\text{A}$	0.8V to 3.6V	—	0.1	—	0.1	V
		$I_{OL} = 1.1\text{mA}$	1.1V	—	$0.3 \times V_{CC}$	—	$0.3 \times V_{CC}$	
		$I_{OL} = 1.7\text{mA}$	1.4V	—	0.31	—	0.37	
		$I_{OL} = 1.9\text{mA}$	1.65V	—	0.31	—	0.35	
		$I_{OL} = 2.3\text{mA}$	2.3V	—	0.31	—	0.33	
		$I_{OL} = 3.1\text{mA}$		—	0.44	—	0.45	
		$I_{OL} = 2.7\text{mA}$	3V	—	0.31	—	0.33	
		$I_{OL} = 4\text{mA}$		—	0.44	—	0.45	
I_I	Input Current	A or B Input $V_I = \text{GND to } 3.6\text{V}$	0V to 3.6V	—	± 0.1	—	± 0.5	μA
I_{OFF}	Power Down Leakage Current	V_I or $V_O = 0\text{V to } 3.6\text{V}$	0	—	0.2	—	0.6	μA
ΔI_{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0\text{V to } 3.6\text{V}$	0V to 0.2V	—	0.2	—	0.6	μA
I_{CC}	Supply Current	$V_I = \text{GND or } V_{CC}, I_O = 0$	0.8V to 3.6V	—	0.5	—	0.9	μA
ΔI_{CC}	Additional Supply Current	One input at $V_{CC} - 0.6\text{V}$ Other inputs at V_{CC} or GND	3.3V	—	40	—	50	μA

Electrical Characteristics (continued) (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vcc	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		Unit
				Min	Max	
V _{IH}	High-Level Input Voltage	—	0.8V to 1.65V	0.80 x V _{CC}	—	V
		—	1.65V to 1.95V	0.70 x V _{CC}	—	
		—	2.3V to 2.7V	1.6	—	
		—	3.0V to 3.6V	2.0	—	
V _{IL}	Low-Level input voltage	—	0.8V to 1.65 V	—	0.25 x V _{CC}	V
		—	1.65V to 1.95V	—	0.30 x V _{CC}	
		—	2.3V to 2.7V	—	0.7	
		—	3.0V to 3.6V	—	0.9	
V _{OH}	High-Level Output Voltage	I _{OH} = -20 μA	0.8V to 3.6V	V _{CC} - 0.11	—	V
		I _{OH} = -1.1 mA	1.1V	0.6 x V _{CC}	—	
		I _{OH} = -1.7 mA	1.4V	0.93	—	
		I _{OH} = -1.9 mA	1.65V	1.17	—	
		I _{OH} = -2.3 mA	2.3V	1.77	—	
		I _{OH} = -3.1 mA		1.67	—	
		I _{OH} = -2.7 mA	3V	2.40	—	
		I _{OH} = -4 mA		2.30	—	
V _{OL}	Low-Level Output Voltage	I _{OL} = 20 μA	0.8 V to 3.6V	—	0.11	V
		I _{OL} = 1.1 mA	1.1V	—	0.33 x V _{CC}	
		I _{OL} = 1.7 mA	1.4V	—	0.41	
		I _{OL} = 1.9 mA	1.65V	—	0.39	
		I _{OL} = 2.3 mA	2.3V	—	0.36	
		I _{OL} = 3.1 mA		—	0.50	
		I _{OL} = 2.7 mA	3V	—	0.36	
		I _{OL} = 4 mA		—	0.50	
I _I	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V	—	± 0.75	μA
I _{OFF}	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0	—	± 3.5	μA
ΔI_{OFF}	Delta Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0V to 0.2V	—	± 2.5	μA
I _{CC}	Supply Current	V _I = GND or V _{CC} , I _O = 0	0.8V to 3.6V	—	3.0	μA
ΔI_{CC}	Additional Supply Current	Input at V _{CC} -0.6V Other inputs at V _{CC} or GND	3.3V	—	75	μA

Switching Characteristics

CL=5pF, See Figure 1

Parameter	From Input	To Output	V _{CC}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t _{pd}	A or B	Y	0.8V	—	17.0	—	—	—	—	—	ns
			1.2V ± 0.1V	2.4	5.1	10.8	2.1	11.7	2.1	12.9	
			1.5V ± 0.1V	1.6	3.7	6.5	1.5	7.5	1.5	8.3	
			1.8V ± 0.15V	1.3	3.0	5.2	1.3	6.1	1.3	6.7	
			2.5V ± 0.2V	1.1	2.4	4.0	1.0	4.8	1.0	5.3	
			3.3V ± 0.3V	1.0	2.2	3.5	0.9	4.3	0.9	4.8	

CL=10pF, See Figure 1

Parameter	From Input	To Output	V _{CC}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t _{pd}	A or B	Y	0.8V	—	20.6	—	—	—	—	—	ns
			1.2V ± 0.1V	2.4	6.0	12.5	2.2	13.6	2.2	15.0	
			1.5V ± 0.1V	2.0	4.3	7.6	1.8	8.9	1.8	9.8	
			1.8V ± 0.15V	1.7	3.6	6.1	1.6	7.2	1.6	7.9	
			2.5V ± 0.2V	1.4	2.9	4.7	1.3	5.7	1.3	6.3	
			3.3V ± 0.3V	1.3	2.7	4.2	1.2	4.7	1.2	5.2	

CL=15pF, See Figure 1

Parameter	From Input	To Output	V _{CC}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t _{pd}	A or B	Y	0.8V	—	24.1	—	—	—	—	—	ns
			1.2V ± 0.1V	3.4	6.8	14.2	3.1	15.7	3.1	17.3	
			1.5V ± 0.1V	2.3	4.9	8.6	2.1	10.1	2.1	11.2	
			1.8V ± 0.15V	1.9	4.0	6.9	1.8	8.2	1.8	9.0	
			2.5V ± 0.2V	1.7	3.4	5.5	1.6	6.5	1.6	7.2	
			3.3V ± 0.3V	1.5	3.1	4.8	1.5	5.9	1.5	6.5	

CL=30pF, See Figure 1

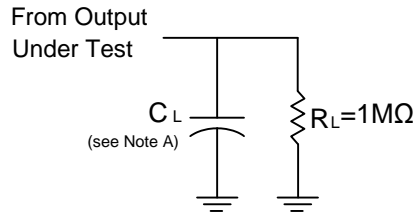
Parameter	From Input	To Output	V _{CC}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
				Min	TYP	Max	Min	Max	Min	Max	
t _{pd}	A or B	Y	0.8V	—	34.4	—	—	—	—	—	ns
			1.2V ± 0.1V	4.0	9.1	19.4	4.0	21.8	4.0	24.0	
			1.5V ± 0.1V	3.2	6.4	11.5	2.9	13.6	2.9	15.0	
			1.8V ± 0.15V	2.6	5.3	9.1	2.4	10.9	2.4	12.1	
			2.5V ± 0.2V	2.3	4.5	7.2	2.2	8.6	2.2	9.5	
			3.3V ± 0.3V	2.1	4.2	6.2	2.1	7.5	2.1	8.3	

Operating and Package Characteristics (@ T_A = +25°C, unless otherwise specified.)

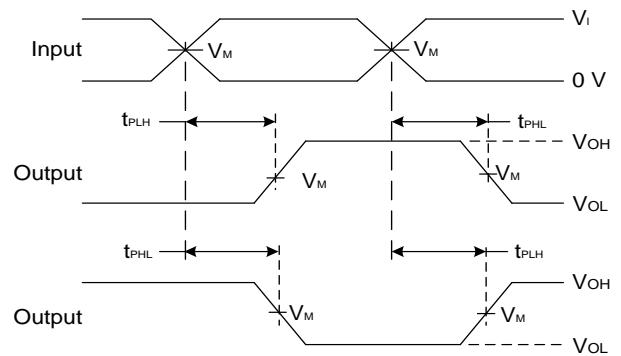
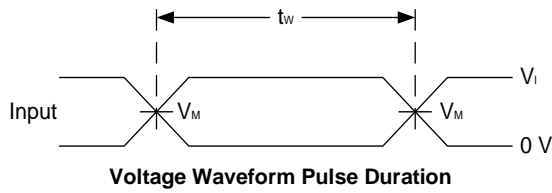
Parameter		Test Conditions		V _{cc}	Typ	Unit
C _{pd}	Power Dissipation Capacitance	f = 1MHz No Load		0.8V	6.7	pF
				1.2V ± 0.1V	6.6	
				1.5V ± 0.1V	6.5	
				1.8V ± 0.15V	6.5	
				2.5V ± 0.2V	6.4	
				3.3V ± 0.3V	6.3	
C _i	Input Capacitance	V _i = V _{cc} or GND		0V or 3.3V	1.5	pF
θ _{JA}	Thermal Resistance Junction-to-Ambient	SOT353	(Note 9)	—	371	°C/W
		X2-DFN0808-4		—	430	
		X1-DFN1010-6		—	435	
		X2-DFN1010-6		—	445	
		X2-DFN1409-6		—	470	
		X2-DFN1410-6		—	460	
θ _{JC}	Thermal Resistance Junction-to-Case	SOT353	(Note 9)	—	143	°C/W
		X2-DFN0808-4		—	240	
		X1-DFN1010-6		—	250	
		X2-DFN1010-6		—	250	
		X2-DFN1409-6		—	275	
		X2-DFN1410-6		—	265	

Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Parameter Measurement Information



V _{CC}	Inputs		V _M	C _L
	V _I	t _r /t _f		
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ±0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V±0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF



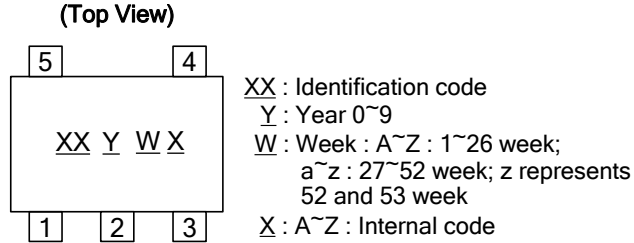
**Voltage Waveform Propagation Delay Times
Inverting and Non Inverting Outputs**

Figure 1 Load Circuit and Voltage Waveforms

- Notes:
- A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate ≤ 10MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLH} and t_{PHL} are the same as t_{PD}.

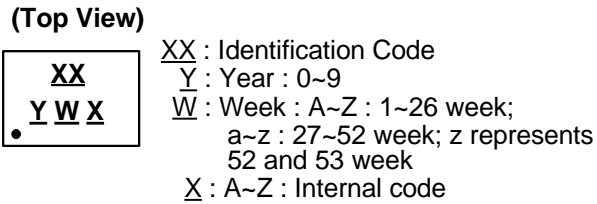
Marking Information

(1) SOT353



Orderable Part Number	Package	Identification Code
74AUP1G08SE	SOT353	XP

(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6

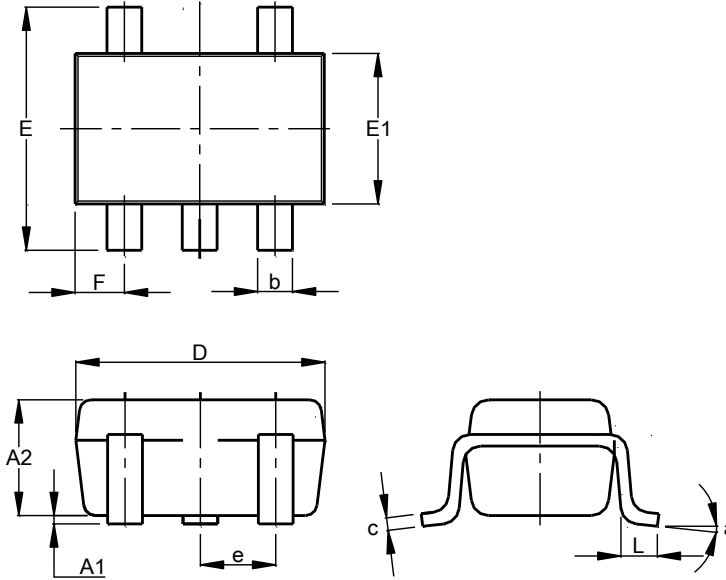


Orderable Part Number	Package	Identification Code
74AUP1G08FS3	X2-DFN0808-4	YR
74AUP1G08FW5	X1-DFN1010-6	Q7
74AUP1G08FW4	X2-DFN1010-6	XP
74AUP1G08FX4	X2-DFN1409-6	HF
74AUP1G08FZ4	X2-DFN1410-6	XP

SOT353 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT353

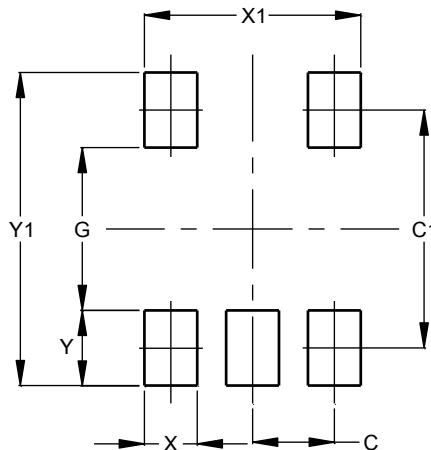


SOT353			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

SOT353 Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT353

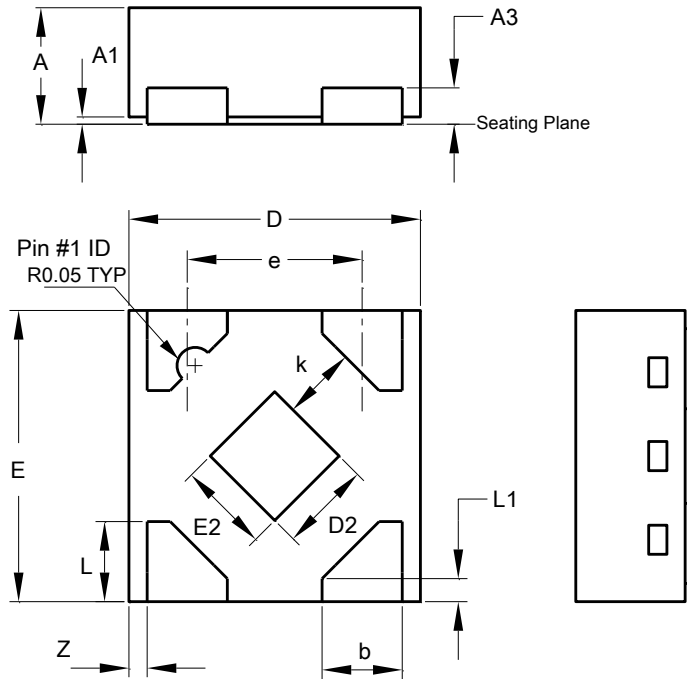


Dimensions	Value (in mm)
C	0.650
C1	1.900
G	1.300
X	0.420
X1	1.720
Y	0.600
Y1	2.500

X2-DFN0808-4 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN0808-4

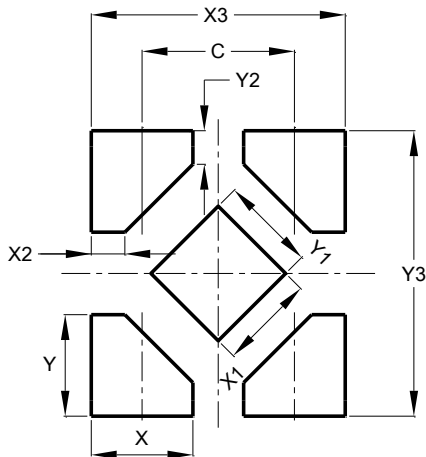


X2-DFN0808-4			
Dim	Min	Max	Typ
A	0.25	0.35	0.30
A1	0	0.04	0.02
A3	-	-	0.13
b	0.17	0.27	0.22
D	0.75	0.85	0.80
D2	0.15	0.35	0.25
E	0.75	0.85	0.80
E2	0.15	0.35	0.25
e	-	-	0.48
K	0.20	-	-
L	0.17	0.27	0.22
L1	0.02	0.12	0.07
Z	-	-	0.05
All Dimensions in mm			

X2-DFN0808-4 Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN0808-4

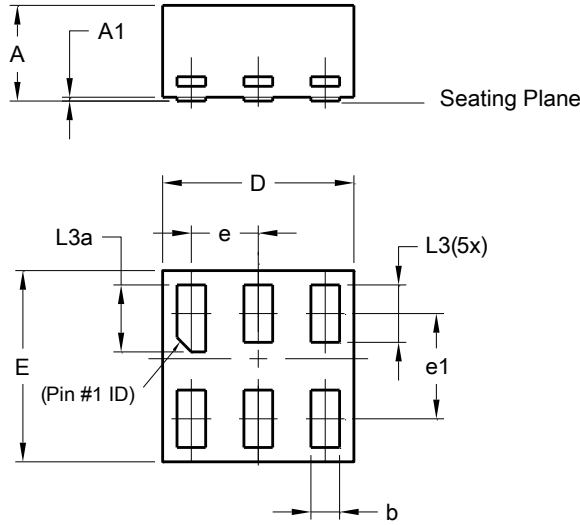


Dimensions	Value
C	0.480
X	0.320
X1	0.300
X2	0.106
X3	0.800
Y	0.320
Y1	0.300
Y2	0.106
Y3	0.900

X1-DFN1010-6 (Type B) Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version

X1-DFN1010-6 (Type B)

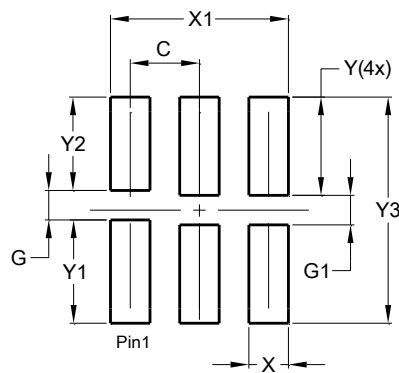


X1-DFN1010-6 (Type B)			
Dim	Min	Max	Typ
A	-	0.50	0.39
A1	-	0.04	-
b	0.12	0.20	0.15
D	0.95	1.050	1.00
E	0.95	1.050	1.00
e	0.35 BSC		
e1	0.55 BSC		
L3	0.27	0.30	0.30
L3a	0.32	0.40	0.35
All Dimensions in mm			

X1-DFN1010-6 (Type B) Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1010-6 (Type B)

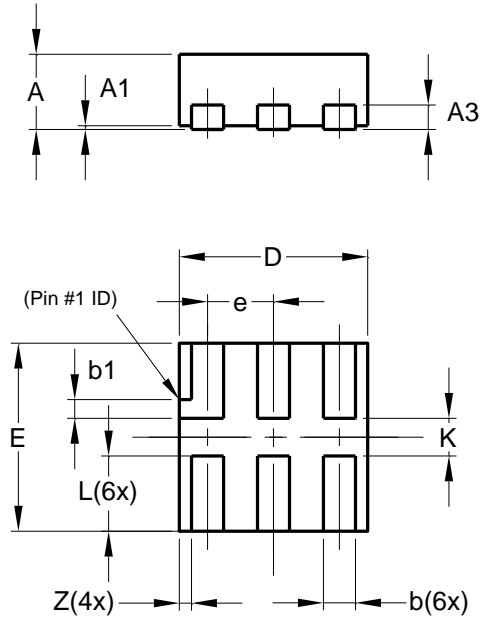


Dimensions	Value (in mm)
C	0.350
G	0.150
G1	0.150
X	0.200
X1	0.900
Y	0.500
Y1	0.525
Y2	0.475
Y3	1.150

X2-DFN1010-6 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version

X2-DFN1010-6

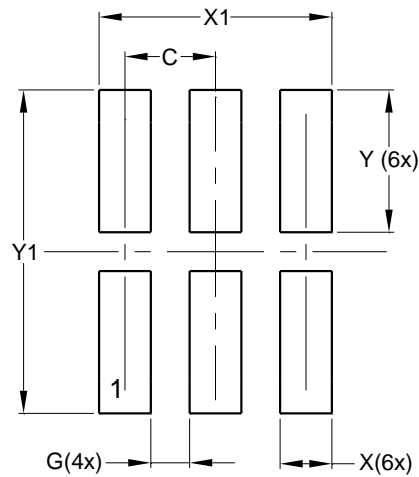


X2-DFN1010-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.14	0.20	0.17
b1	0.05	0.15	0.10
D	0.95	1.05	1.00
E	0.95	1.05	1.00
e	—	—	0.35
L	0.35	0.45	0.40
K	0.15	—	—
Z	—	—	0.065
All Dimensions in mm			

X2-DFN1010-6 Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1010-6

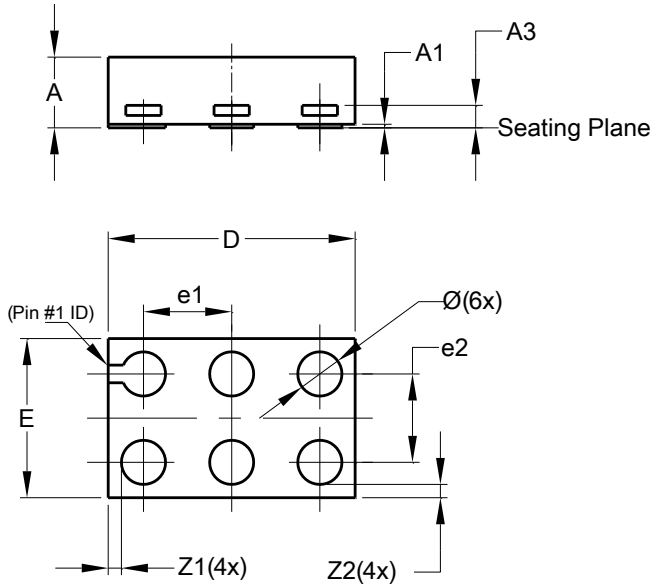


Dimensions	Value (in mm)
C	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

X2-DFN1409-6 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version

X2-DFN1409-6

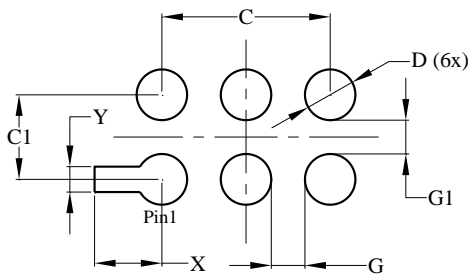


X2-DFN1409-6			
Dim	Min	Max	Typ
A	-	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.13
∅	0.20	0.30	0.25
D	1.35	1.45	1.40
E	0.85	0.95	0.90
e1	-	-	0.50
e2	-	-	0.50
Z1	-	-	0.075
Z2	-	-	0.075
All Dimensions in mm			

X2-DFN1409-6 Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1409-6

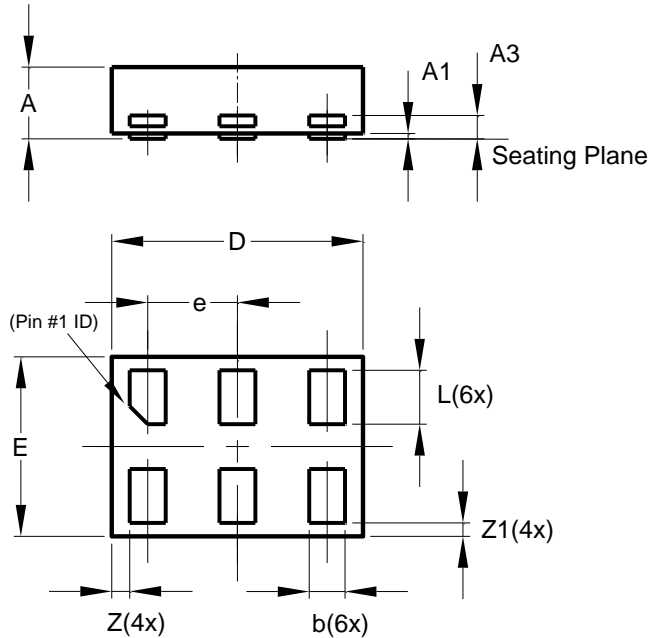


Dimensions	Value (in mm)
C	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
X	0.400
Y	0.150

X2-DFN1410-6 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version

X2-DFN1410-6

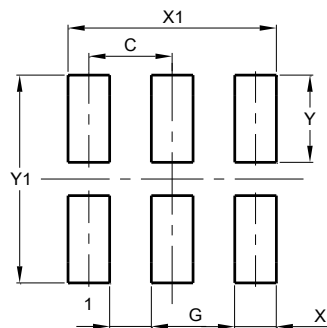


X2-DFN1410-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
e	—	—	0.50
L	0.25	0.35	0.30
Z	—	—	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			

X2-DFN1410-6 Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1410-6



Dimensions	Value (in mm)
C	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

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